

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

Device	V _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
Q1	30V	1.5Ω @ $V_{GS} = 4.5V$	350mA
Qi	307	2.0Ω @ $V_{GS} = 2.5V$	SSUTIA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features

- Low On-Resistance: R_{DS(ON)}
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

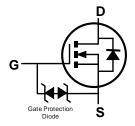
- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208[®]
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)

SOT523

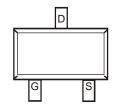




Top View



Equivalent Circuit



Top View Pin Out Configuration

Ordering Information (Note 4)

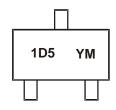
Part Number	Case	Packaging
DMN31D6UT-7	SOT523	3,000/Tape & Reel
DMN31D6UT-13	SOT523	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



1D5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014)M = Month (ex: 9 = September)

Date Code Key

Year	2014	2	2015	2016		2017	2018		2019	2020		2021
Code	В		С	D		E	F		G	Н		1
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Au	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current (Note 6)	Continuous	I _D	350	mA
Pulsed Drain Current (Note 6)		I _{DM}	800	mA

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)		P _D	210	mW	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Ъ	593	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	$R_{\theta JA}$	542	C/VV	
Total Power Dissipation (Note 6)		P_{D}	320	mW	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Ъ	398	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	363	C/VV	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

Notes:

^{5.} Device mounted on FR-4 PCB, with minimum recommended pad layout 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.

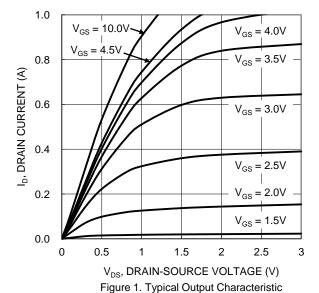


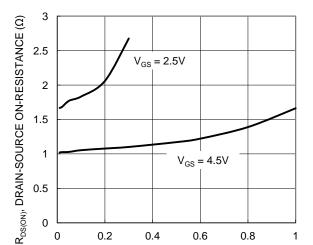
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
DFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current @T _C = +25°0	C I _{DSS}	_	_	100	nA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.4	_	1.4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	1.1	1.5	Ω	$V_{GS} = 4.5V, I_D = 100mA$	
Static Dialii-Source Off-Nesistance	R _{DS(ON)}	_	1.6	2.0	1 12	$V_{GS} = 2.5V, I_D = 50mA$	
Diode Forward Voltage	V_{SD}	_	0.6	1.0	V	$V_{GS} = 0V$, $I_S = 10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	13.6	_	pF		
Output Capacitance		_	3.1	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	2.2	_	pF	1.500112	
Total Gate Charge	Q_g	_	0.35	_	nC	45)	
Gate-Source Charge	Q_{gs}	_	0.06	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $V_{DS} = 15V,$	
Gate-Drain Charge		_	0.19	_	nC	-1D = 20011IA	
Turn-On Delay Time	t _{D(ON)}	_	3.3	_	ns		
Turn-On Rise Time		_	2.3	_	ns	$V_{DD} = 15V, V_{GS} = 4.5V,$	
Turn-Off Delay Time		_	7.4	_	ns	$R_G = 2\Omega$, $I_D = 200$ mA	
Turn-Off Fall Time		_	4.4	_	ns		

7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A)
Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

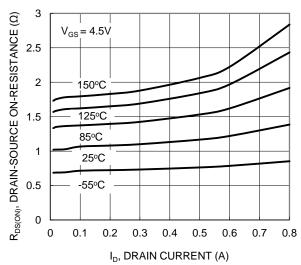
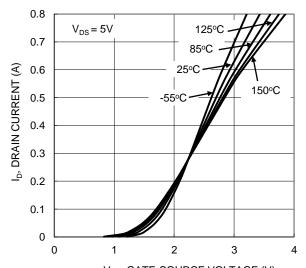


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

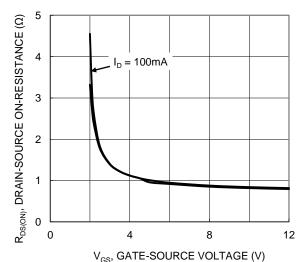


Figure 4. Typical Transfer Characteristic

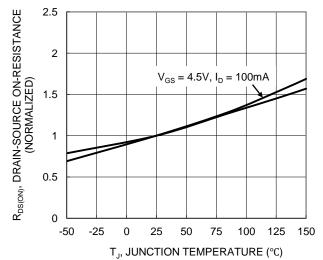
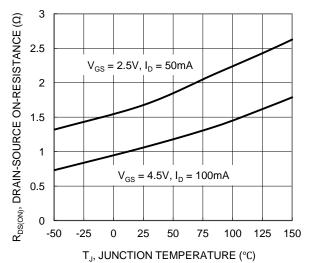


Figure 6. On-Resistance Variation with Junction Temperature





Figue 7. On-Resistance Variation with Junction Temperature

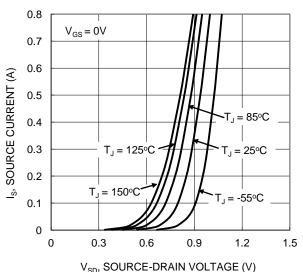


Figure 9. Diode Forward Voltage vs. Current

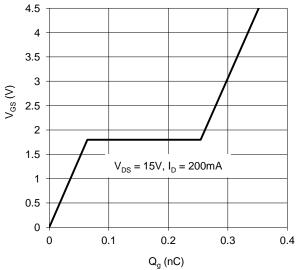


Figure 11. Gate Charge

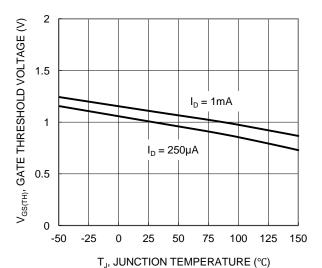


Figure 8. Gate Threshold Variation vs. Junction Temperature

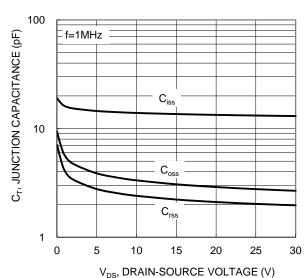


Figure 10. Typical Junction Capacitance

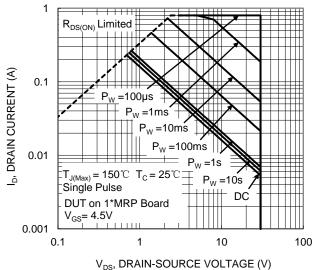


Figure 12. SOA, Safe Operation Area



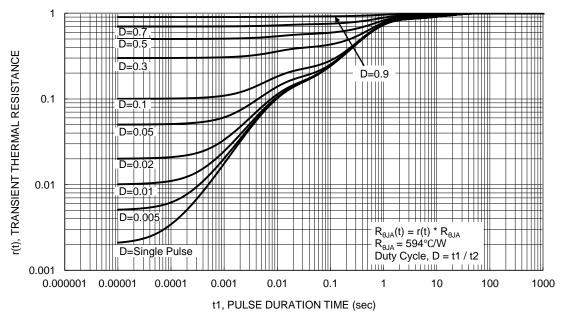


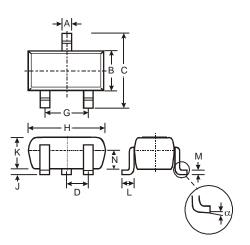
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

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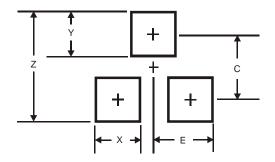


SOT523							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.22				
В	0.75	0.85	0.80				
၁	1.45	1.75	1.60				
D			0.50				
G	0.90	1.10	1.00				
H	1.50	1.70	1.60				
7	0.00	0.10	0.05				
K	0.60	0.80	0.75				
L	0.10	0.30	0.22				
M	0.10	0.20	0.12				
N	0.45	0.65	0.50				
α	0°	8°	_				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT523



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
E	0.7



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